

Low-Voltage, Low R_{ON}, Dual DPDT Analog Switch

DESCRIPTION

The DG2015 is a dual double-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed, low on-resistance and small physical size, the DG2015 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2015 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-beforemake is guaranteed.

The switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FEATURES

- Low Voltage Operation (2.7 V to 3.3 V)
- Low On-Resistance ${\rm R_{ON}}{:}~0.85~\Omega$
- 3 dB Loss at 100 MHz
- Fast Switching: $t_{ON} = 40 \text{ ns}$ $t_{OFF} = 35 \text{ ns}$

QFN-16 Package

Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



HALOGEN FREE

BENEFITS

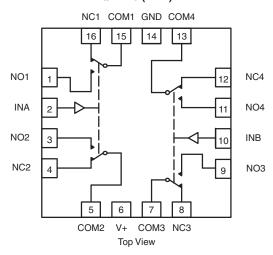
- **Reduced Power Consumption**
- High Accuracy
- Reduced Board Space
- Reduce Board Space
- TTL/1.8 V Logic Compatible

APPLICATIONS

- Cellular Phones
- Speaker Headset Switching
- Audio and Video Signal Routing
- **PCMCIA Cards**
- **Battery Operated Systems**

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRUTH TABLE								
Logic	NC1, 2, 3 and 4	NO1, 2, 3 and 4						
0	ON	OFF						
1	OFF	ON						

ORDERING INFORMATION								
Temp Range	Package	Part Number						
	16-pin QFN							
- 40 °C to 85 °C	(4 mm x 4 mm)	DG2015DN-T1-E4						
	(Variation 1)							

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ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
Parameter	Limit	Unit						
Reference V+ to GND	- 0.3 to + 6	.,,						
IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)	V						
Current (Any terminal except NO, NC or C	30							
Continuous Current (NO, NC, or COM)	± 150	mA						
Peak Current (Pulsed at 1 ms, 10 % duty	± 200							
Storage Temperature (D Suffix)	- 65 to 150	00						
Package Solder Reflow Conditions ^d	240	°C						
Power Dissipation (Packages) ^b	1880	mW						

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 23.5 mW/°C above 70 °C.
- d. Manual soldering with iron is not recommended for leadless components. The QFN is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

		Test Conditions Otherwise Unless Specified		- 40	Unit			
Parameter	Symbol	$V+ = 3 V$, $\pm 10 \%$, $V_{IN} = 0.4 V$ or $2 V^e$	Temp.a	Min.b	Typ. ^c	Max.b		
Analog Switch	•							
Analog Signal Range ^d	$V_{NO}, V_{NC} V_{COM}$		Full	0		V+	V	
On-Resistance	R _{ON}	$V+ = 2.7 \text{ V}, V_{COM} = 0.2 \text{ V}/1.5 \text{ V}, I_{NO}, I_{NC} = 100 \text{ mA}$	Room Full		0.85	1.6 1.7		
R _{ON} Flatness	R _{ON} Flatness	V+ = 2.7 V, V _{COM} = 0 V to V+, I _{NO} , I _{NC} = 100 mA			0.16		Ω	
R _{ON} Match	ΔR_{ON}		Room		0.15			
Switch Off	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V	Room Full	- 1 - 10		1 10		
Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V/3 V}$, $V_{COM} = 3 \text{ V/1 V}$		- 1 - 10		1 10	nA	
Channel-On Leakage Current	I _{COM(on)}	$V+ = 3.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 1 \text{ V/3 V}$	Room Full	- 1 - 10		1 10		
Digital Control	•							
Input High Voltage V _{INI}			Full	2			V	
Input Low Voltage	V _{INL}		Full			0.4	V	
Input Capacitance	C _{in}		Full		4		pF	
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ V or V} +$	Full	- 1		1	μΑ	
Dynamic Characteristics								
Turn-On Time	t _{ON}		Room Full		40	65 67		
Turn-Off Time	t _{OFF}	V_{NO} or V_{NC} = 2 V, R_L = 300 Ω , C_L = 35 pF			35	60 62	ns	
Break-Before-Make Time	eak-Before-Make Time t _d		Full	1	3			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega$	Room		7		рC	
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 1 MHz$	Room		- 67		10	
Crosstalk ^d	X _{TALK}	$\frac{1}{1} = \frac{1}{2} $ $\frac{1}{2} $	Room		- 70		dB	
N. N. Off Conneitons ed	C _{NO(off)}		Room		63			
N _O , N _C Off Capacitance ^d	C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz			67		pF	
Channel On Canaditars and	C _{NO(on)}	V _{IN} = 0 v 01 v+, 1 = 1 WI112	Room		200		pi.	
Channel-On Capacitance ^d	C _{NC(on}		Room		196			



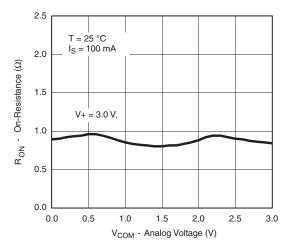


SPECIFICATIONS (V+ = 3 V)									
		Test Conditions Otherwise Unless Specified				s °C	Unit		
Parameter	Temp.a	Min.b	Typ. ^c	Max.b					
Power Supply									
Power Supply Range	V+			2.7		3.3	V		
Power Supply Current	I+	V _{IN} = 0 V or V+	Full			1	μΑ		
Power Consumption	P _C	VIN = 0 V 01 V+	Full			3.3	μW		

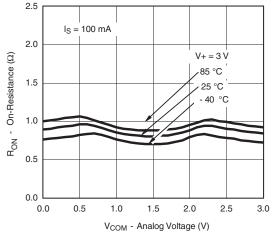
- a. Room = 25 °C, full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

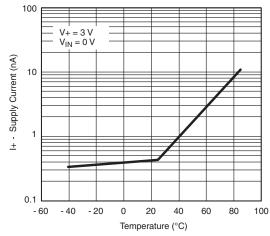
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



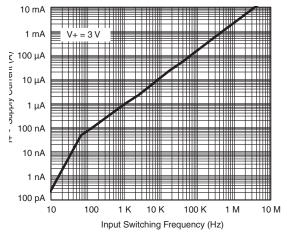
 R_{ON} vs. V_{COM} and Supply Voltage



R_{ON} vs. Analog Voltage and Temperature



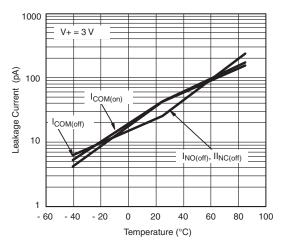
Supply Current vs. Temperature



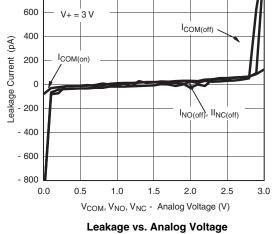
Supply Current vs. Input Switching Frequency

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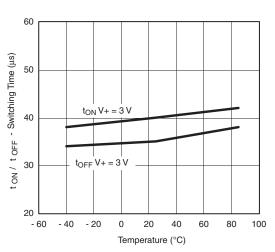
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



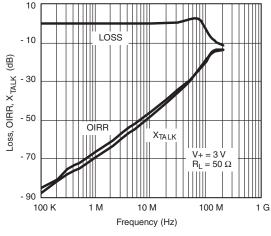
Leakage Current vs. Temperature



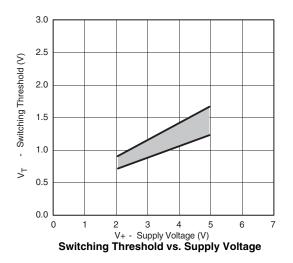
800

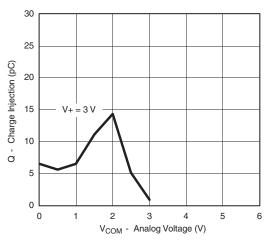


Switching Time vs. Temperature



Insertion Loss, Off-Isolation Crosstalk vs. Frequency

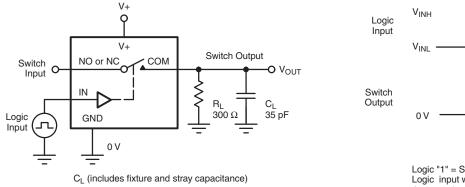




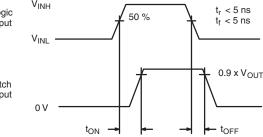
Charge Injection vs. Analog Voltage



TEST CIRCUITS



$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

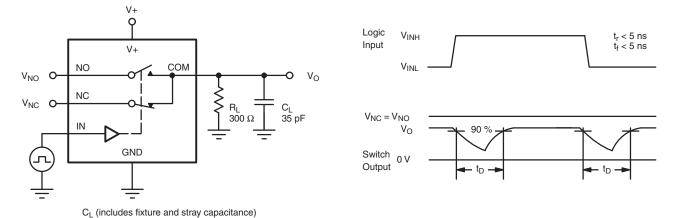


Figure 2. Break-Before-Make Interval

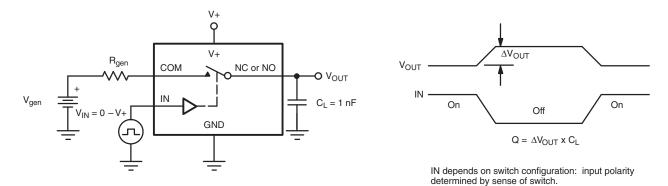


Figure 3. Charge Injection

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TEST CIRCUITS

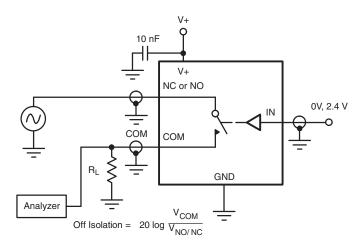


Figure 4. Off-Isolation

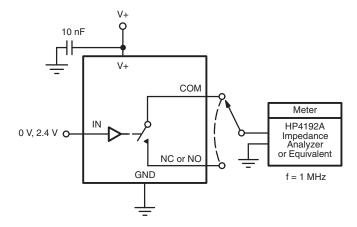
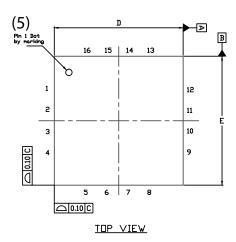


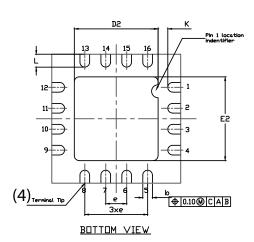
Figure 5. Channel Off/On Capacitance

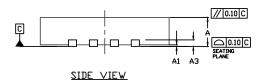
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71971.



QFN 4x4-16L Case Outline







	VARIATION 1						VARIATION 2					
DIM	MILLIMETERS ⁽¹⁾		INCHES		MILLIMETERS ⁽¹⁾			INCHES				
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
A3		0.20 ref.		0.008 ref.		0.20 ref.			0.008 ref.			
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014
D		4.00 BSC		0.157 BSC		4.00 BSC			0.157 BSC			
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.098 0.102 0.10	
е		0.65 BSC		0.026 BSC		0.65 BSC			0.026 BSC			
Е		4.00 BSC		0.157 BSC		4.00 BSC		0.157 BSC				
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
K		0.20 min			0.008 min.		0.20 min.		0.008 min.			
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020
N ⁽³⁾		16		16		16		16				
Nd ⁽³⁾		4			4		4 4					
Ne ⁽³⁾		4			4		4 4					

Notes

- ⁽¹⁾ Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

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DWG: 5890

Revision: 22-Apr-13



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